

200 Form PTO-1112		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1208		SERIAL NO. 09/388,826	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Weimin Li et al.			
				FILING DATE September 1, 1999		GROUP 2813	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EK	AA	5,883,011	4/1999	Lin et al			
↑	AB	4,805,683	2/1989	Magdo et al			
	AC	5,874,367	2/1999	Dobson			
	AD	5,858,880	1/1999	Dobson et al			
	AE	5,219,613	6/1993	Fabry et al			
	AF	5,270,267	12/1993	Quellet			
	AG	5,541,445	7/1996	Quellet			
	AH	6,022,404	2/2000	Ettlinger et al			
	AI	5,709,741	1/1998	Akamatsu et al			
	AJ	4,648,904	3/1987	Depasquale et al			
	AK	4,158,717	6/1979	Nelson			
	AL	5,667,015	9/1997	Harestad et al			
	AM	5,661,093	8/1997	Ravi et al			
	AN	5,536,857	7/1996	Naula			
	AO	4,695,859	9/1987	Guha et al			
	AP	4,954,867	6/1990	Hosaka			
	AQ	5,441,797	8/1995	Hogan			
	AR	5,710,067	1/1998	Foote			
	AS	5,759,755	6/1998	Park et al			
	AT	5,838,052	11/1998	McTeer			
✓	AU	5,061,509	10/1991	Naito et al			
EK	AV	4,600,671	7/1986	Saitoh et al			

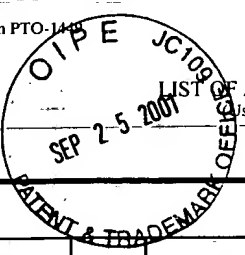
EXAMINER

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12/19/01

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Form PTO-1470		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1208		SERIAL NO. 09/388,826	
 LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Weimin Li et al.			
				FILING DATE September 1, 1999		GROUP 2813	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EK	BA	5,753,320	5/1998	Mikoshiba et al			
↑	BB	5,356,515	10/1994	Tahara et al			
	BC	5,674,356	10/07/97	Nagayama			
	BD	5,731,242	03/24/98	Parat et al.			
	BE	5,741,721	04/21/98	Stevens			
	BF	5,034,348	07/23/91	Hartswick et al.			
	BG	5,472,829	12/05/95	Ogawa			
	BH	5,641,607	06/24/97	Ogawa et al.			
	BI	5,648,202	07/15/97	Ogawa et al.			
	BJ	5,670,297	09/23/97	Ogawa et al.			
	BK	5,677,111	10/14/97	Ogawa			
	BL	5,698,352	12/16/97	Ogawa et al.			
	BM	5,831,321	11/03/98	Nagayama			
	BN	5,591,566	01/07/97	Ogawa			
	BO	6,008,124	12/28/99	Sekiguchi et al.			
	BP	5,340,621	08/23/94	Matsumoto et al.			
	BQ	5,600,165	02/04/97	Tsukamoto et al.			
	BR	5,872,385	02/16/99	Taft et al.			
	BS	5,960,289	09/28/99	Tsui et al.			
	BT	5,968,324	10/19/99	Cheung et al.			
✓	BU	6,020,243	02/01/00	Wallace et al.			
EK	BV	5,472,827	12/1995	Ogawa et al.			
EXAMINER <i>Erik Kuhn</i>				DATE CONSIDERED 12/19/07			
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Weimin Li et al.			
					FILING DATE September 1, 1999		GROUP 2813	
U.S. PATENT DOCUMENTS								
*Examiner Initial	CA	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
EC	CA	4,474,975	10-84	Clemons et al.				
↑	CB	5,962,581	10-99	Hayase et al.				
	CC	6,140,151	10-00	Akram				
	CD	5,314,724	5-94	Tsukune et al.				
	CE	5,376,591	12-94	Maeda et al.				
	CF	5,817,549	10-98	Yamazaki et al.				
	CG	6,072,227	6-00	Yau et al.				
	CH	6,001,741	12-99	Alers				
	CI	5,786,039	7-98	Brouquet				
	CJ	6,235,568 B1	5/01	Murthy				
	CK	6,187,694 B1	2/01	Cheng				
	CL	5,750,442	5/98	Juengling				
	CM	6,114,255	9/00	Juengling				
	CN	6,238,976	5/01	Noble				
	CO	6,008,121	12/99	Yang				
	CP	5,140,390	8/92	Li				
	CQ	5,286,661	2/94	de Fresart				
	CR	6,184,151	2/01	Adair				
	CS	6,225,217 B1	5/01	Usami				
	CT	6,004,850	12/99	Lucas				
	CU	6,140,677	10/00	Gardner				
	CV	6,133,096	10/00	Su				
	CW	6,136,636	10/00	Wu				
	CX	5,933,721	8/99	Hause				
	CY	5,981,368	11/99	Gardner				
	CZ	6,159,804	12/00	Gardner				
	C1	6,130,168	10/00	Chu				
✓	C2	6,235,591	5/01	Balasubramanian				
EC	C3	6,198,144 B1	3/01	Pan				
EXAMINER <i>E. K. Kiehl</i>				DATE CONSIDERED <i>12/19/01</i>				
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OTHER REFERENCES (including Article Title, Date, Pertinent Pages, Etc.)					
EX	EA		TEXT: Jenkins, F. et al., "Fundamentals of Optics", Properties of Light, pp. 9-10. (No date)		
↑	EB		TEXT: Wolf, S. et al., "Silicon Processing for the VLSI Era", Vol. 1, pp. 437-441. (No date)		
	EC		D.R. McKenzie et al., "New Technology for PACVD", Surface and Coatings Technology, 82 (1996), pp. 326-333.		
	ED		S. McClatchie et al.; "Low Dielectric Constant Flowfill® Technology For IMD Applications"; undated; 7 pages		
	EF		K. Beekmann et al.; "Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology"; October 1995; pp. 1-7		
	EH		A. Kiermasz et al.; "Planarisation for Sub-Micron Devices Utilising a New Chemistry"; Electrotech, February 1995; 2 pages		
	EI		IBM Technical Disclosure Bulletin "Low-Temperature Deposition of SiO ₂ , Si ₃ N ₄ or SiO ₂ -Si ₃ N ₄ ," Vol. 28, No. 9, p. 4170, Feb. 1986.		
	EJ		ARTICLE: Bencher, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp.109-114.		
	EH		Noboru Shibata, "Plasma-Chemical Vapor-Deposited Silicon Oxide/Silicon Oxynitride Double-Layer Antireflective Coating for Solar Cells", Japanese Journal of Applied Physics, Vol. 30, No. 5, May 1991, pp. 997-1001.		
	EL		Ralls, Kenneth M., "Introduction to Materials Science and Engineering", John Wiley & Sons, © 1976, pp. 312-313		
	EM		Ravi K. Laxman, "Synthesizing Low-k CVD Materials for Fab Use", Semiconductor International, Nov. 2000, 10 pps.		
	EN		Anonymous, "New gas helps make faster IC's, Machine Design Cleveland, © Penton Media, Inc., November 4, 1999, pp. 118		
	EO		Lobada et al, "Using Trimethylsilane to Improve Safety Throughput and Versatility in PECVD Processes", 4th International Symposium on Silicon Nitride and Silicon Dioxide Thin Insulating Films, The Electrochemical Society, Abstract No. 358, p. 454, May 1997.		
	EP		ARTICLE: Dammel, R. R. et al., "Dependence of Optical Constants of AZ® BARLi™ Bottom Coating on Back Conditions", SPIE Vol. 3049 (1997), pp. 963-973.		
	EQ		TEXT: Heavens, O. S., "Optical Properties of Thin Solid Films", pp. 48-49.		
	ER		Withmall, R. et al., "Matrix Reactions of Methylsilanes and Oxygen Atoms", Phys. Chem 1988, pp. 594-602.		
	ES		Weidman, T. et al., "New photodefinable glass etch masks for entirely dry photolithography: Plasma deposited ororganosilicon hydride polymers", Appl. Phys. Lett 1-25-93, pp. 372-374.		
	ET		Weidman, et al., "All Dry Lithography: Applications of Plasma Polymerized Methylsilane as a Single Layer Resist and Silicon Dioxide Precursor", Journal of Photopolymer Science and Technology, V. 8, #4, 1995, pp. 679-686.		
	EU		Joubert et al., "Application of Plasma Polymerized Methylsilane in an all dry resist process for 193 and 248 nm Lithography", Microelectronic Engineering 30 (1996), pp. 275-278.		
	EV		Joshi, A.M. et al., "Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography, SPIE Vol. 1925, pp. 709-720.		
↓	EW		Matsura, M. et al., "Highly Reliable Self-Planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects", IEEE 1997, pp. 785-788.		
EX	EX		Horie, O. et al., "Kinetics and Mechanism of the Reactions of ...", J. Phys. Chem 1991, 4393-4400.		
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[Signature]			12/19/01		
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